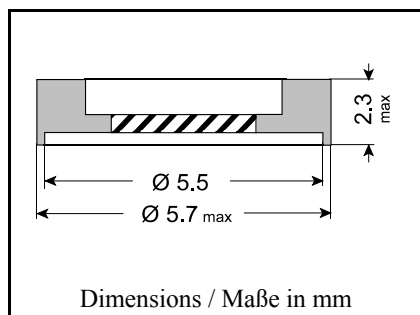


**Silicon Rectifier Cells
with polysiloxan passivation**
**Silizium-Gleichrichterzellen
mit Polysiloxan-Passivierung**


| | |
|---|-------------|
| Nominal current – Nennstrom | 6 A |
| Repetitive peak reverse voltage Periodische Spitzensperrspannung | 50...1000 V |
| Weight approx. – Gewicht ca. | 0.3 g |
| Standard packaging bulk Standard Lieferform lose | |

Maximum ratings and Characteristics
Kenn- und Grenzwerte

| Type Typ | Repetitive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V] | Surge peak reverse voltage Stoßspitzensperrspannung V_{RSM} [V] |
|-------------|--|---|
| AG 6A | 50 | 80 |
| AG 6B | 100 | 130 |
| AG 6D | 200 | 250 |
| AG 6G | 400 | 450 |
| AG 6J | 600 | 700 |
| AG 6K | 800 | 1000 |
| AG 6M | 1000 | 1300 |

| | | | |
|--|---------------------------|--------------------|--|
| Max. forward rectified current, R-load Dauergrenzstrom in Einwegschaltung mit R-Last | $T_T = 100^\circ\text{C}$ | I_{FAV} | 6 A ¹⁾ |
| Repetitive peak forward current Periodischer Spitzenstrom | $f > 15\text{ Hz}$ | I_{FRM} | 40 A ¹⁾ |
| Peak forward surge current, 50 Hz half sine-wave Stoßstrom für eine 50 Hz Sinus-Halbwellen | $T_A = 25^\circ\text{C}$ | I_{FSM} | 400 A |
| Rating for fusing – Grenzlastintegral, $t < 10\text{ ms}$ | $T_A = 25^\circ\text{C}$ | i^2t | 800 A ² s |
| Operating junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur | | T_j T_s | $-50...+150^\circ\text{C}$ $-50...+150^\circ\text{C}$ |
| Forward voltage Durchlaßspannung | $T_j = 25^\circ\text{C}$ | $I_F = 6\text{ A}$ | $V_F < 0.95\text{ V}$ |
| Leakage current – Sperrstrom | $T_j = 25^\circ\text{C}$ | $V_R = V_{RRM}$ | $I_R < 10\ \mu\text{A}$ |

¹⁾ Max. temperature of the terminals $T_T = 100^\circ\text{C}$ – Max. Temperatur der Kontaktflächen $T_T = 100^\circ\text{C}$